

FORM PTO-1449				Atty. Docket No. XA-9945		Appln. No.	
LIST OF DOCUMENTS CITED BY APPLICANT				Applicant Tomoyuki ISHII et al.			
				Filing Date HEREWITH		Group	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
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FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
ah	AJ	2001-156275	6/08/01	Japan			Abstract
	AK						
	AL						
	AM						
	AN						
	AO						
OTHER (including author, title, date, pertinent pages, etc.)							
ah	AP	Arai, et al., "High-Density (4.4F ²) NAND Flash Technology Using Super-Shallow Channel Profile (SSCP) Engineering," IEEE International Electron Devices Meeting 2000, pp. 775-778.					
ah	AQ	Kobayashi, et al., "A Giga-Scale Assist-Gate (AG)-(AND)-Type Flash Memory Cell with 20-MB/s Programming Throughput for Content-Downloading Applications," IEEE International Electron Devices Meeting 2001 pp. 29-32.					
ah	AR	Eitan, et al., "Can NROM, a 2 Bit, Trapping Storage NVM Cell, Give a Real Challenge to Floating Gate Cells?" International Conference on Solid State Devices and Materials 1999, pp. 522-524.					
Examiner Admeyer				Date Considered 08/08/05			
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